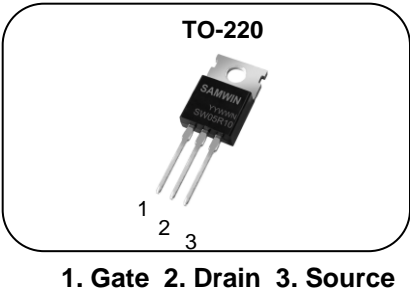


N-channel Enhanced mode TO-220 MOSFET

Features

- High ruggedness
- Low  $R_{DS(ON)}$  (Typ 3.7mΩ)@ $V_{GS}=10V$   
Low  $R_{DS(ON)}$  (Typ 5.3mΩ)@ $V_{GS}=4.5V$
- Low Gate Charge (Typ 132nC)
- Improved dv/dt Capability
- 100% Avalanche Tested
- Application: Synchronous Rectification, Li Battery Protect Board, Inverter



**$BV_{DSS}$  : 100V**  
 **$I_D$  : 50A**  
 **$R_{DS(ON)}$  : 3.7mΩ @ $V_{GS}=10V$   
5.3mΩ @ $V_{GS}=4.5V$**

A schematic symbol for an N-channel MOSFET, showing the gate, drain, and source terminals.

General Description

This power MOSFET is produced with advanced technology of SAMWIN. This technology enable the power MOSFET to have better characteristics, including Fast switching time, low on resistance, low gate charge and especially excellent Avalanche characteristics.



Order Codes

Item	Sales Type	Marking	Package	Packaging
1	SW P 05R10	SW05R10	TO-220	TUBE

Absolute maximum ratings

Symbol	Parameter	Value	Unit
$V_{DSS}$	Drain to source voltage	100	V
$I_D$	Continuous drain current (@ $T_C=25^{\circ}C$ )	50*	A
	Continuous drain current (@ $T_C=100^{\circ}C$ )	31.5*	A
$I_{DM}$	Drain current pulsed (note 1)	200	A
$V_{GS}$	Gate to source voltage	$\pm 20$	V
$E_{AS}$	Single pulsed avalanche energy (note 2)	1223	mJ
$E_{AR}$	Repetitive avalanche energy (note 1)	68	mJ
dv/dt	Peak diode recovery dv/dt (note 3)	5	V/ns
$P_D$	Total power dissipation (@ $T_C=25^{\circ}C$ )	260	W
	Derating factor above 25°C	2	W/°C
$T_{STG}, T_J$	Operating junction temperature & storage temperature	-55 ~ + 150	°C
$T_L$	Maximum lead temperature for soldering purpose, 1/8 from case for 5 seconds.	300	°C

\*. Drain current is limited by junction temperature.

Thermal characteristics

Symbol	Parameter	Value	Unit
$R_{thjc}$	Thermal resistance, Junction to case	0.48	°C/W
$R_{thja}$	Thermal resistance, Junction to ambient	52	°C/W

Electrical characteristic (  $T_C = 25^\circ\text{C}$  unless otherwise specified )

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
<b>Off characteristics</b>						
$BV_{DSS}$	Drain to source breakdown voltage	$V_{GS}=0V, I_D=250\mu A$	100			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown voltage temperature coefficient	$I_D=250\mu A$ , referenced to $25^\circ\text{C}$		0.06		V/ $^\circ\text{C}$
$I_{DSS}$	Drain to source leakage current	$V_{DS}=100V, V_{GS}=0V$			1	$\mu A$
		$V_{DS}=80V, T_C=125^\circ\text{C}$			50	$\mu A$
$I_{GSS}$	Gate to source leakage current, forward	$V_{GS}=20V, V_{DS}=0V$			100	nA
	Gate to source leakage current, reverse	$V_{GS}=-20V, V_{DS}=0V$			-100	nA
<b>On characteristics</b>						
$V_{GS(TH)}$	Gate threshold voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.7		2.5	V
$R_{DS(ON)}$	Drain to source on state resistance	$V_{GS}=10V, I_D=30A$		3.7	5	m $\Omega$
		$V_{GS}=4.5V, I_D=30A$		5.3	6.5	m $\Omega$
$G_{fs}$	Forward transconductance	$V_{DS}=10V, I_D=30A$		98		S
<b>Dynamic characteristics</b>						
$C_{iss}$	Input capacitance	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$		7290		pF
$C_{oss}$	Output capacitance			2990		
$C_{rss}$	Reverse transfer capacitance			283		
$t_{d(on)}$	Turn on delay time	$V_{DS}=50V, I_D=30A, R_G=25\Omega, V_{GS}=10V$ (note 4,5)		47		ns
$t_r$	Rising time			125		
$t_{d(off)}$	Turn off delay time			425		
$t_f$	Fall time			244		
$Q_g$	Total gate charge	$V_{DS}=80V, V_{GS}=10V, I_D=30A$ (note 4,5)		132		nC
$Q_{gs}$	Gate-source charge			24		
$Q_{gd}$	Gate-drain charge			39		
$R_g$	Gate resistance	$V_{DS}=0V$ , Scan F mode		1.9		$\Omega$

## Source to drain diode ratings characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous source current	Integral reverse p-n Junction diode in the MOSFET			50	A
$I_{SM}$	Pulsed source current				200	A
$V_{SD}$	Diode forward voltage drop.	$I_S=50A, V_{GS}=0V$			1.4	V
$t_{rr}$	Reverse recovery time	$I_S=30A, V_{GS}=0V,$ $dI_F/dt=100A/\mu s$		80		ns
$Q_{rr}$	Reverse recovery charge			175		nC

### ※. Notes

- Repetitive rating : pulse width limited by junction temperature.
- $L=2.7\text{mH}, I_{AS}=30A, V_{DD}=50V, R_G=25\Omega$ , Starting  $T_J=25^\circ\text{C}$
- $I_{SD} \leq 30A, di/dt = 100A/\mu s, V_{DD} \leq BV_{DSS}$ , Starting  $T_J=25^\circ\text{C}$
- Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
- Essentially independent of operating temperature.

Fig. 1. On-state characteristics

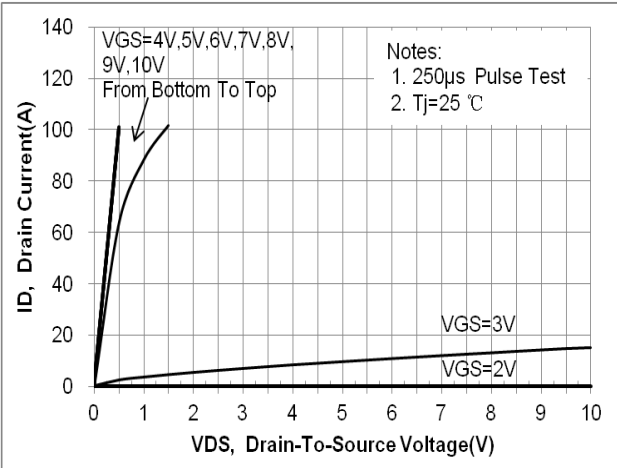


Fig. 2. On-resistance variation vs. drain current and gate voltage

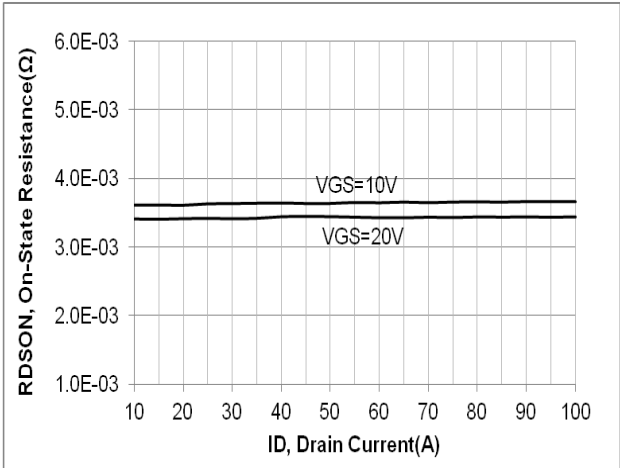


Fig. 3. Gate charge characteristics

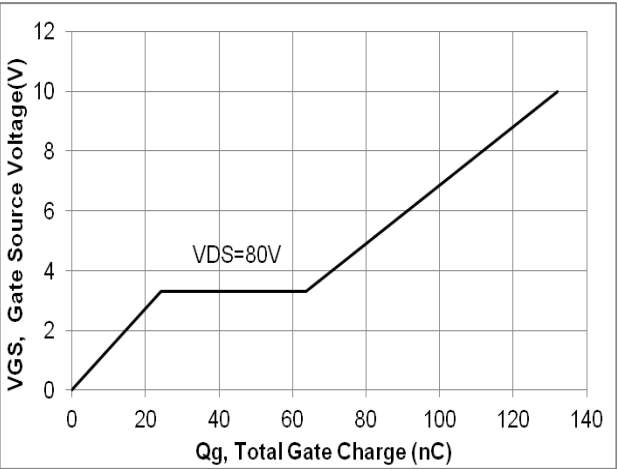


Fig. 4. On state current vs. diode forward voltage

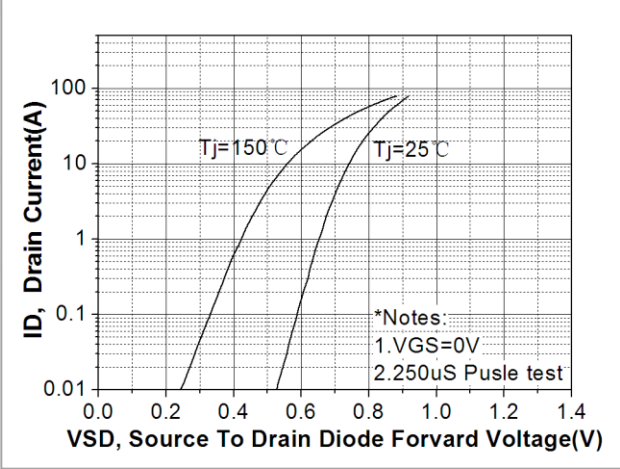


Fig 5. Breakdown Voltage Variation vs. Junction Temperature

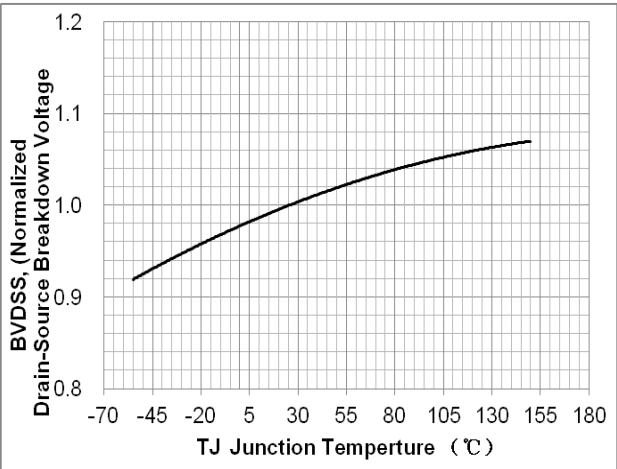


Fig. 6. On resistance variation vs. junction temperature

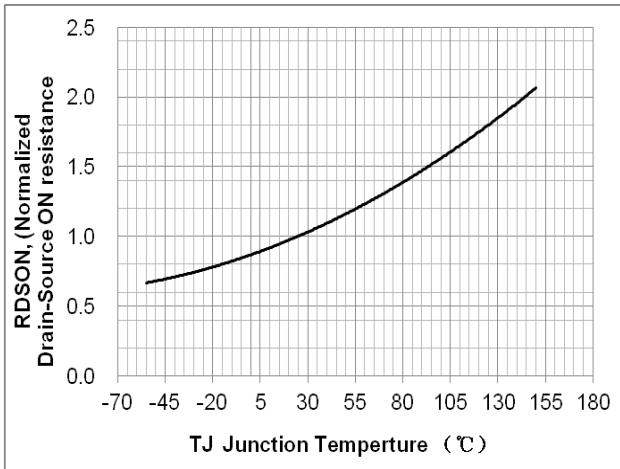


Fig. 7. Maximum safe operating area

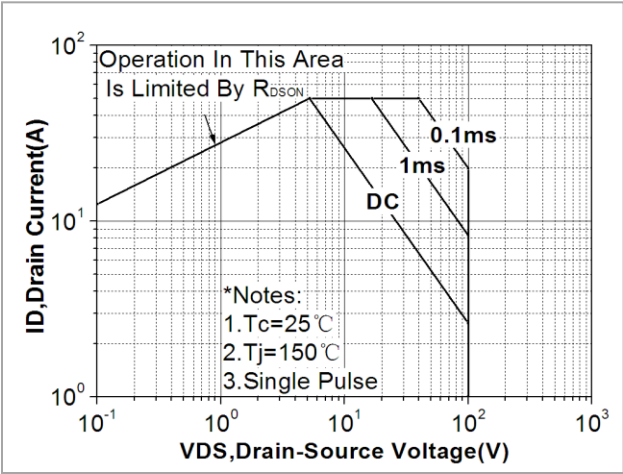


Fig. 8. Capacitance Characteristics

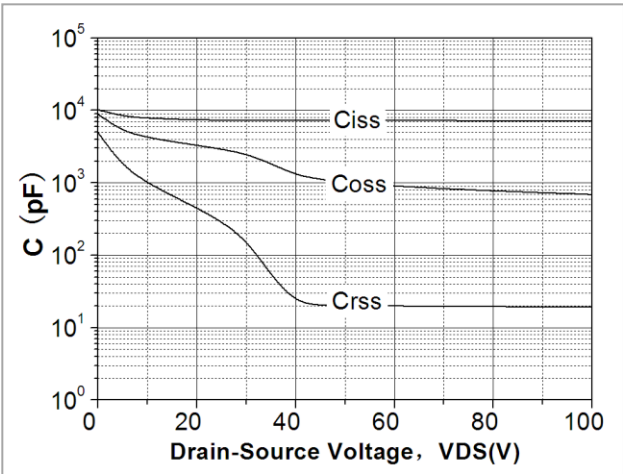


Fig. 9. Transient thermal response curve

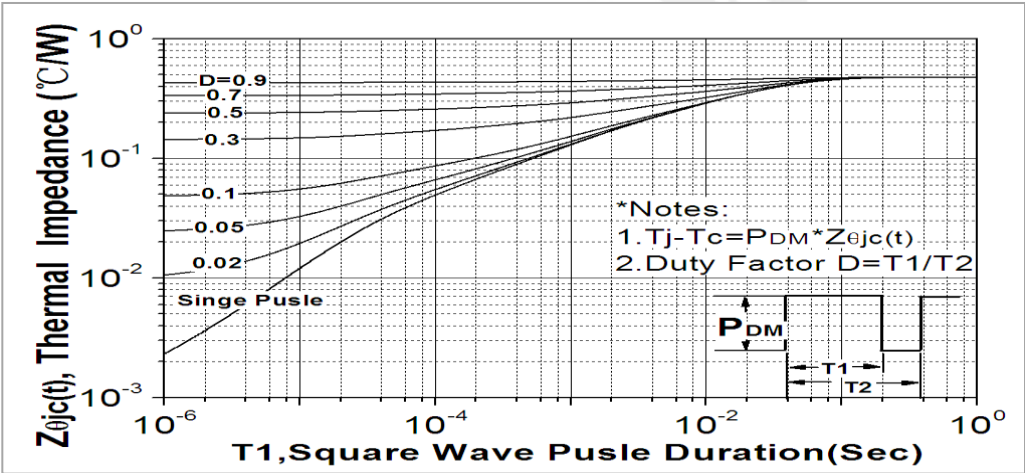


Fig. 10. Gate charge test circuit & waveform

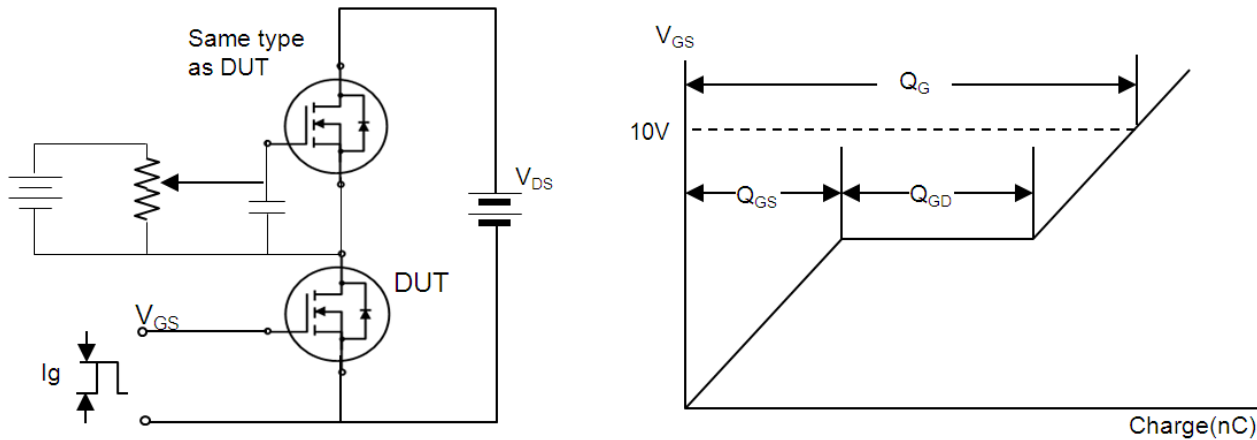


Fig. 11. Switching time test circuit & waveform

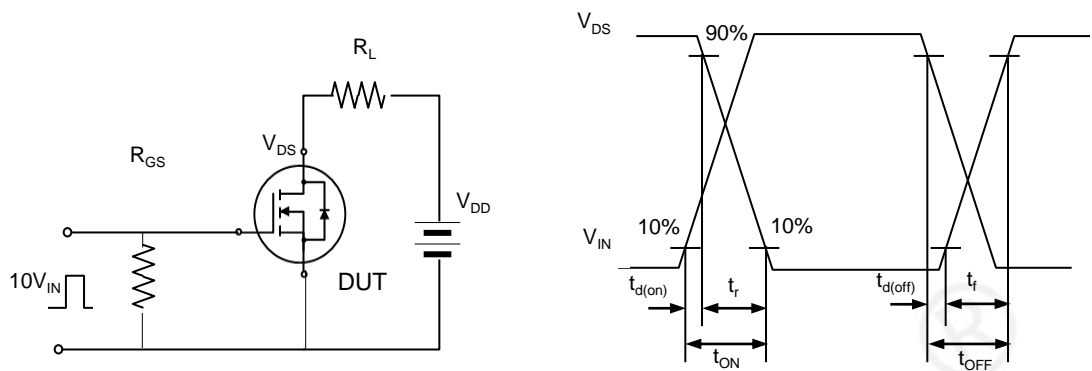


Fig. 12. Unclamped Inductive switching test circuit & waveform

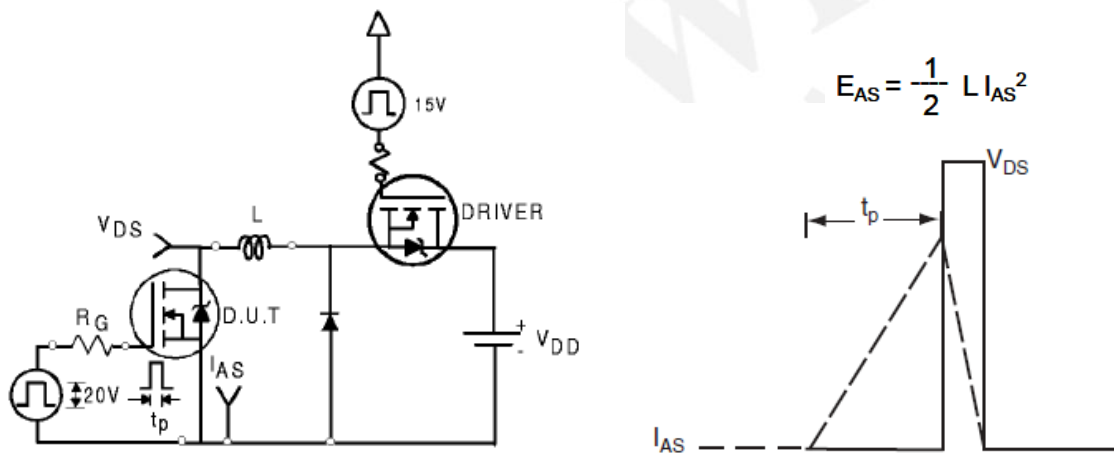
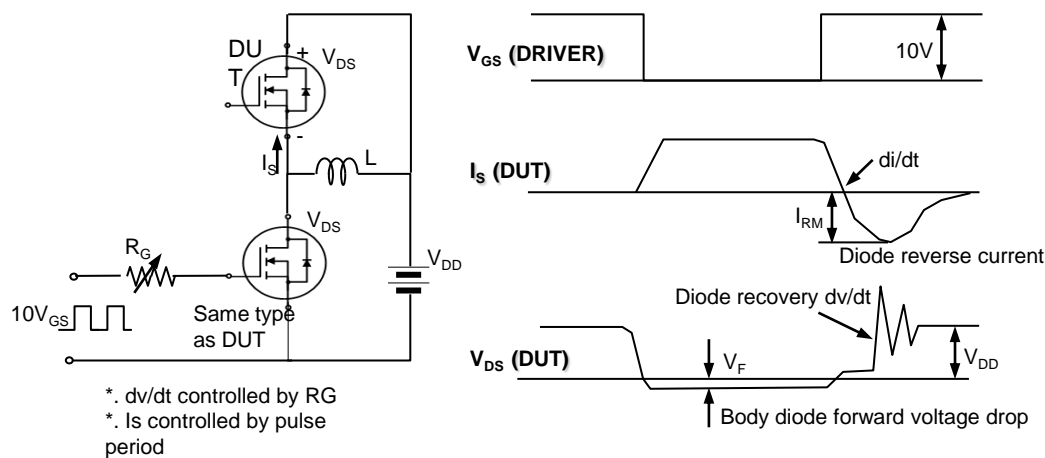



Fig. 13. Peak diode recovery dv/dt test circuit & waveform



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### DISCLAIMER

- \* All the data & curve in this document was tested in XI'AN SEMIPOWER TESTING & APPLICATION CENTER.
- \* This product has passed the PCT,TC,HTRB,HTGB,HAST,PC and Solderdunk reliability testing.
- \* Qualification standards can also be found on the Web site (<http://www.semipower.com.cn>) 
- \* Suggestions for improvement are appreciated, Please send your suggestions to [samwin@samwinsemi.com](mailto:samwin@samwinsemi.com)